

ON Semiconductor

Is Now

The logo for onsemi, featuring the word "onsemi" in a dark teal, lowercase, sans-serif font. The letter "i" is stylized with a white dot and a teal vertical bar. A small orange triangle is positioned above the top right of the "i". A trademark symbol (TM) is located to the right of the logo.

To learn more about onsemi™, please visit our website at
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ON Semiconductor®

FDD8444L-F085

N-Channel PowerTrench[®] MOSFET

40V, 50A, 6.0mΩ

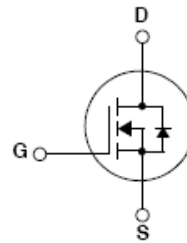
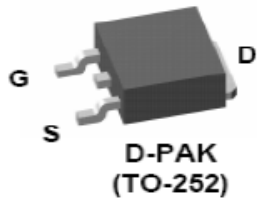
Features

- Typ $r_{DS(on)} = 3.8m\Omega$ at $V_{GS} = 5V$, $I_D = 50A$
- Typ $Q_{g(tot)} = 46nC$ at $V_{GS} = 5V$
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse/ Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant



Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Transmission
- Distributed Power Architecture and VRMs
- Primary Switch for 12V and 24V systems



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	40	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current Continuous ($T_C < 150^\circ\text{C}$, $V_{GS} = 10\text{V}$) (Note 1)	50	A
	Continuous ($T_{amb} = 25^\circ\text{C}$, $V_{GS} = 10\text{V}$, with $R_{\theta JA} = 52^\circ\text{C/W}$)	16	
	Pulsed	See Figure 4	
E_{AS}	Single Pulse Avalanche Energy (Note 2)	295	mJ
P_D	Power Dissipation	153	W
	Derate above 25°C	1.02	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature	-55 to +175	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.98	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO-252, 1in^2 copper pad area	52	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8444L	FDD8444L-F085	TO-252AA	13"	12mm	2500 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

B_{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{V}$, $V_{GS} = 0\text{V}$ $T_J = 150^\circ\text{C}$	-	-	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	1	1.8	3	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 50\text{A}$, $V_{GS} = 10\text{V}$	-	3.5	5.2	m Ω
		$I_D = 50\text{A}$, $V_{GS} = 5\text{V}$	-	3.8	6.0	
		$I_D = 50\text{A}$, $V_{GS} = 4.5\text{V}$	-	4.0	6.5	
		$I_D = 50\text{A}$, $V_{GS} = 5\text{V}$, $T_J = 175^\circ\text{C}$	-	6.8	10.7	

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	5530	-	pF	
C_{oss}	Output Capacitance		-	605	-	pF	
C_{rss}	Reverse Transfer Capacitance		-	400	-	pF	
R_G	Gate Resistance	$f = 1\text{MHz}$	-	1.7	-	Ω	
$Q_{g(TOT)}$	Total Gate Charge at 5V	$V_{GS} = 0$ to 5V	$V_{DD} = 20\text{V}$ $I_D = 50\text{A}$ $I_g = 1.0\text{mA}$	-	46	60	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0$ to 2V		-	5.4	7	nC
Q_{gs}	Gate to Source Gate Charge			-	16.3	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau			-	10.9	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	21	-	nC

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
t_{on}	Turn-On Time	$V_{DD} = 20\text{V}, I_D = 50\text{A}$ $V_{GS} = 5\text{V}, R_{GS} = 2\Omega$	-	-	104	ns
$t_{d(on)}$	Turn-On Delay Time		-	18.7	-	ns
t_r	Turn-On Rise Time		-	46	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	42	-	ns
t_f	Turn-Off Fall Time		-	19.2	-	ns
t_{off}	Turn-Off Time		-	-	96	ns

Drain-Source Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 50\text{A}$	-	0.9	1.25	V
		$I_{SD} = 25\text{A}$	-	0.8	1.0	
t_{rr}	Reverse Recovery Time	$I_F = 50\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	34	44	ns
Q_{rr}	Reverse Recovery Charge		-	29	38	nC

Notes:

- 1: Package current limitation is 50A.
- 2: Starting $T_J = 25^\circ\text{C}$, $L = 0.37\text{mH}$, $I_{AS} = 40\text{A}$.

Typical Characteristics

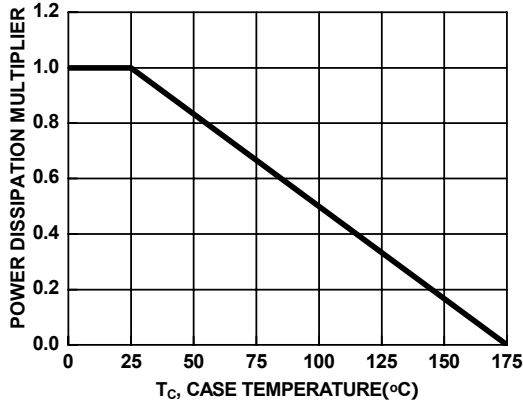


Figure 1. Normalized Power Dissipation vs Case Temperature

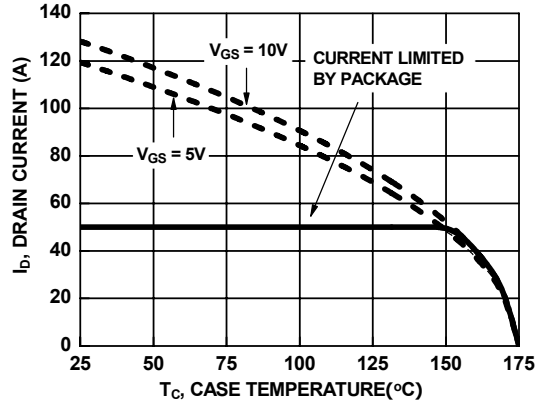


Figure 2. Maximum Continuous Drain Current vs Case Temperature

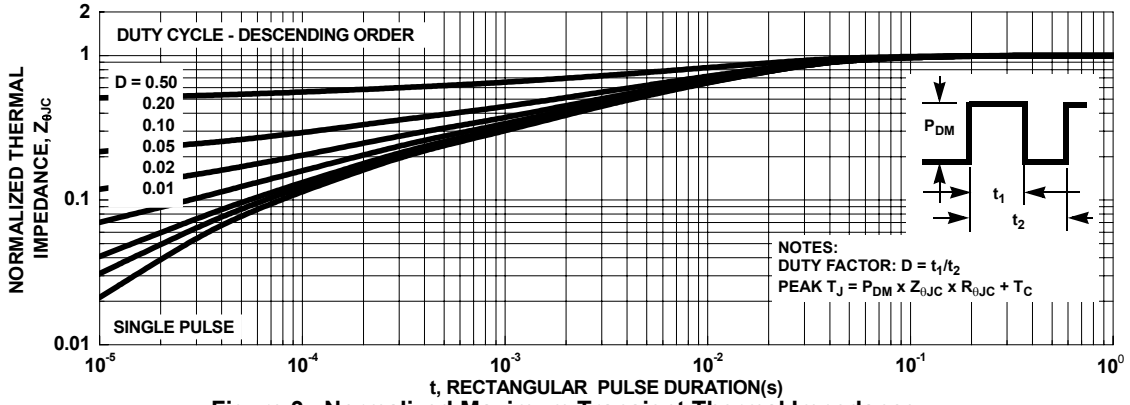


Figure 3. Normalized Maximum Transient Thermal Impedance

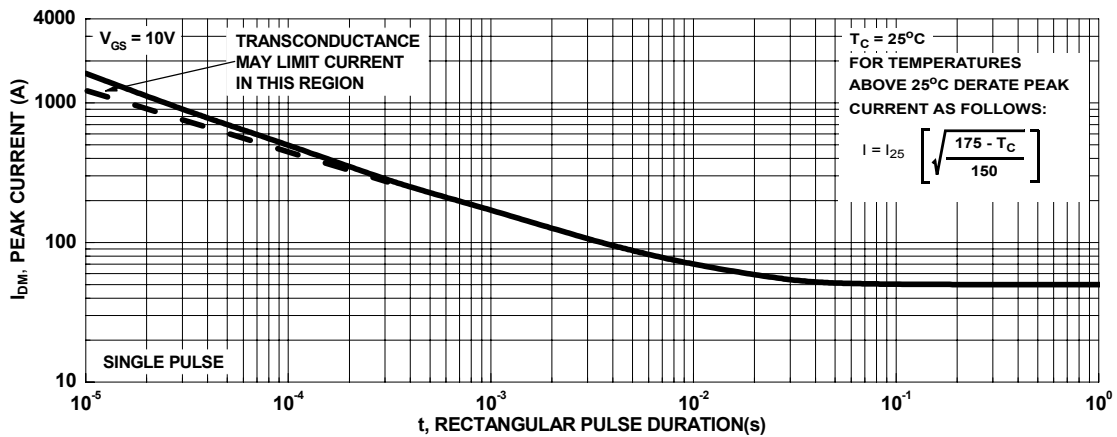


Figure 4. Peak Current Capability

Typical Characteristics

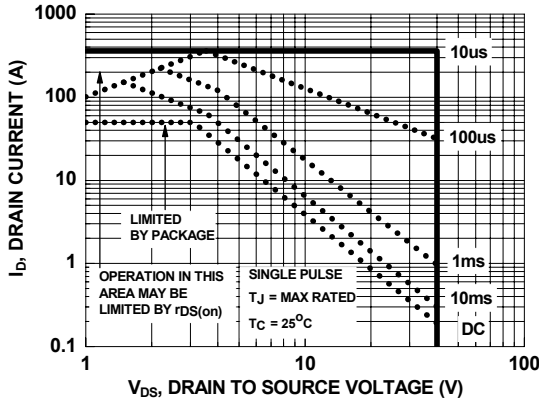


Figure 5. Forward Bias Safe Operating Area

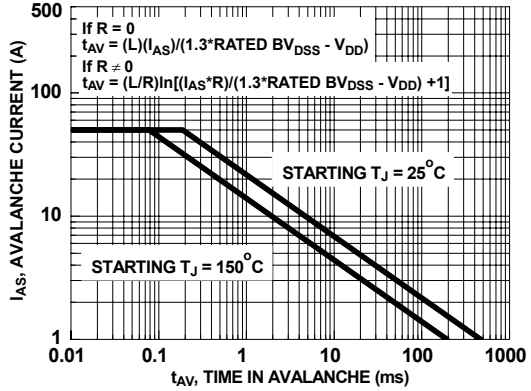


Figure 6. Unclamped Inductive Switching Capability

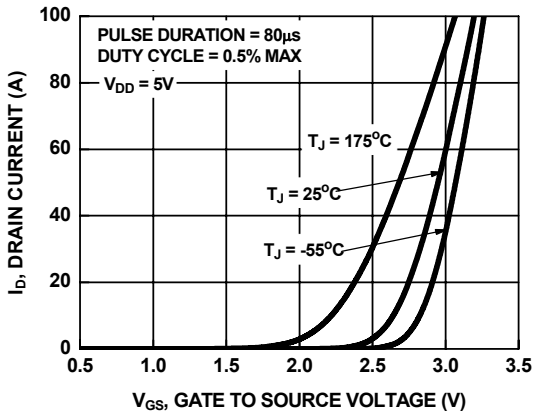


Figure 7. Transfer Characteristics

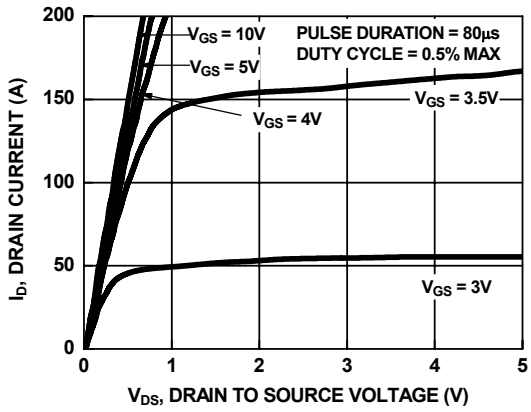


Figure 8. Saturation Characteristics

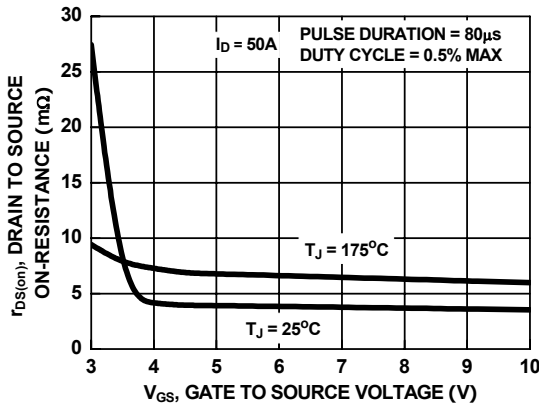


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

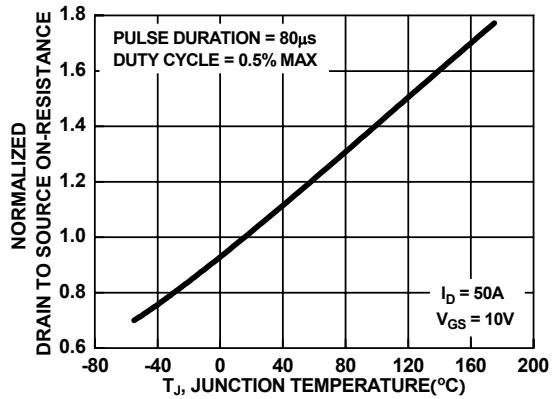


Figure 10. Normalized Drain to Source On-Resistance vs Junction Temperature

Typical Characteristics

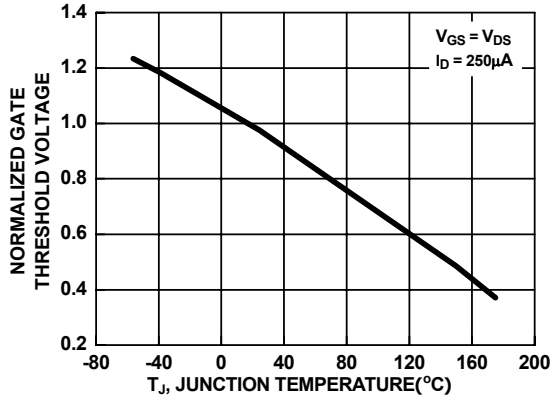


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

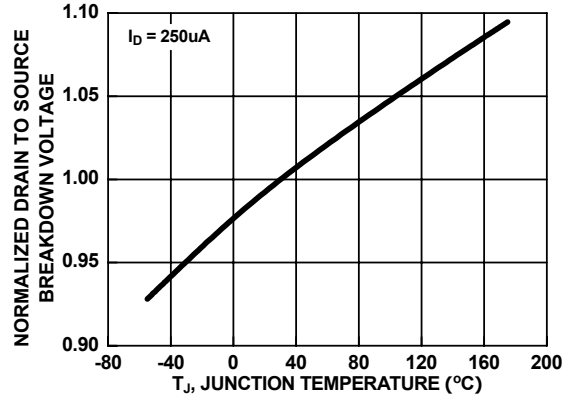


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

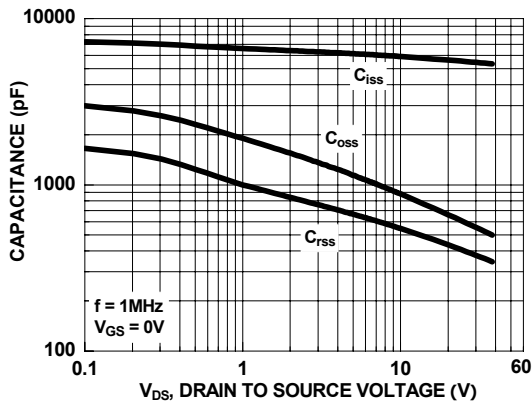


Figure 13. Capacitance vs Drain to Source Voltage

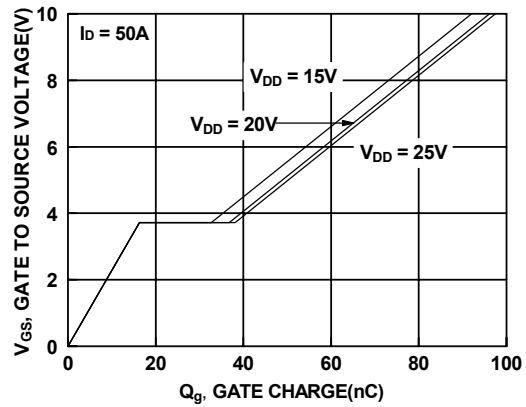



Figure 14. Gate Charge vs Gate to Source Voltage

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